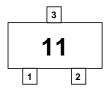


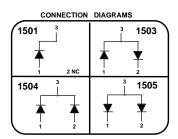
Discrete POWER & Signal **Technologies** 

# MMBD1501/A / 1503/A / 1504/A / 1505/A





#### MMBD1501 11 MMBD1501A A11 MMBD1503 13 MMBD1503A A13 MMBD1504 14 MMBD1504A A14 MMBD1505 15 MMBD1505A A15



# **High Conductance Low Leakage Diode**

Sourced from Process 1L.

# **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
W <sub>IV</sub>	Working Inverse Voltage	180	V
Io	Average Rectified Current	200	mA
I <sub>F</sub>	DC Forward Current	600	mA
İf	Recurrent Peak Forward Current	700	mA
İ <sub>f(surge)</sub>	Peak Forward Surge Current Pulse width = 1.0 second Pulse width = 1.0 microsecond	1.0 2.0	A A
T <sub>stg</sub>	Storage Temperature Range	-55 to +150	°C
TJ	Operating Junction Temperature	150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

## **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
		MMBD1501/A/ 1503-1505/A*		
P <sub>D</sub>	Total Device Dissipation	350	mW	
	Derate above 25°C	2.8	mW/°C	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W	

<sup>\*</sup>Device mounted on glass epoxy PCB 1.6" X 1.6" X 0.06"; mounting pad for the collector lead min. 0.93 in2

# **High Conductance Low Leakage Diode**

(continued)

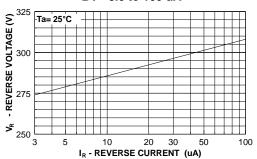
### **Electrical Characteristics**

TA = 25°C unless otherwise noted

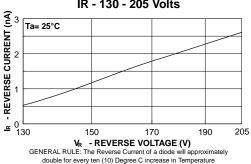
Symbol	Parameter	Test Conditions	Min	Max	Units
$B_V$	Breakdown Voltage	$I_R = 5.0 \mu A$	200		V
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 125 V V <sub>R</sub> = 125 V, T <sub>A</sub> = 150°C V <sub>R</sub> = 180 V V <sub>R</sub> = 180 V, T <sub>A</sub> = 150°C		1.0 3.0 10 5.0	nA μA nA μA
V <sub>F</sub>	Forward Voltage	$I_{F} = 1.0 \text{ mA}$ $I_{F} = 10 \text{ mA}$ $I_{F} = 50 \text{ mA}$ $I_{F} = 100 \text{ mA}$ $I_{F} = 200 \text{ mA}$ $I_{F} = 300 \text{ mA}$	620 720 800 830 0.87 0.9	720 830 890 930 1.1 1.15	mV mV mV mV V
Co	Diode Capacitance	$V_R = 0$ , $f = 1.0 \text{ MHz}$		4.0	pF

# **Typical Characteristics**

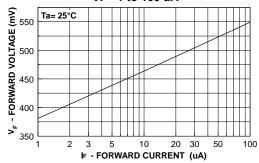
### REVERSE VOLTAGE vs REVERSE CURRENT BV - 3.0 to 100 uA



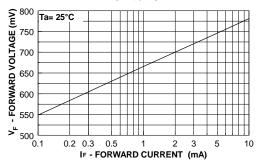
### REVERSE CURRENT vs REVERSE VOLTAGE IR - 130 - 205 Volts



# FORWARD VOLTAGE vs FORWARD CURRENT VF - 1 to 100 uA



# FORWARD VOLTAGE vs FORWARD CURRENT VF - 0.1 to 10 mA

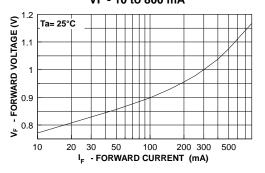


# **High Conductance Low Leakage Diode**

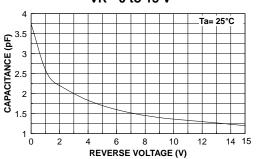
(continued)

# Typical Characteristics (continued)

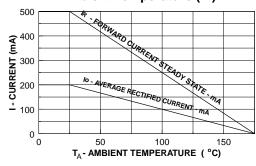
# FORWARD VOLTAGE vs FORWARD CURRENT VF - 10 to 800 mA



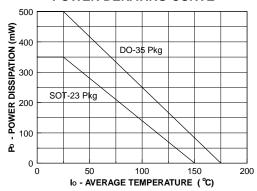
# CAPACITANCE vs REVERSE VOLTAGE VR - 0 to 15 V



# Average Rectified Current (Io) & Forward Current (Ir) versus Ambient Temperature (TA)



### **POWER DERATING CURVE**



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FACT Quiet Series  $^{\text{TM}}$  Quiet Series  $^{\text{TM}}$  SuperSOT  $^{\text{TM}}$ -3 SuperSOT  $^{\text{TM}}$ -6 GTO  $^{\text{TM}}$  SuperSOT  $^{\text{TM}}$ -8 HiSeC  $^{\text{TM}}$  TinyLogic  $^{\text{TM}}$ 

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